

Ordering number : ENN7531

N-Channel Silicon MOSFET

**MCH3443**

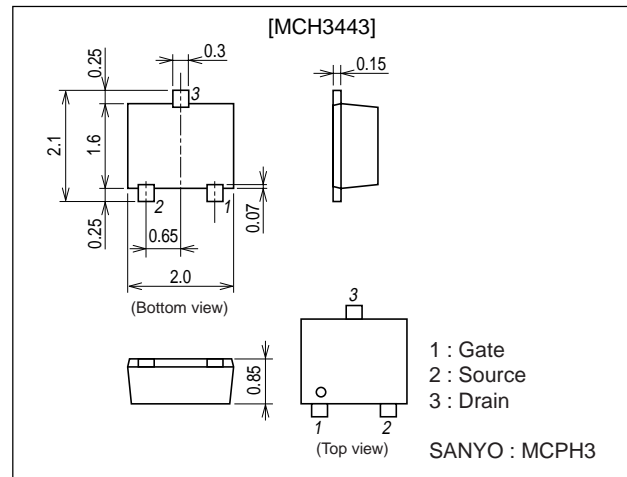
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm
2167A



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|------------------|--|-------------|------|
| Drain-to-Source Voltage | V _{DSS} | | 30 | V |
| Gate-to-Source Voltage | V _{GSS} | | ±12 | V |
| Drain Current (DC) | I _D | | 1.5 | A |
| Drain Current (Pulse) | I _{DP} | PW≤10μs, duty cycle≤1% | 6 | A |
| Allowable Power Dissipation | P _D | Mounted on a ceramic board (900mm ² X0.8mm) | 0.8 | W |
| Channel Temperature | T _{ch} | | 150 | °C |
| Storage Temperature | T _{stg} | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|----------------------|--|---------|-----|-----|------|
| | | | min | typ | max | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | I _D =1mA, V _{GS} =0 | 30 | | | V |
| Zero-Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0 | | | 1 | μA |
| Gate-to-Source Leakage Current | I _{GSS} | V _{GS} =±8V, V _{DS} =0 | | | ±10 | μA |
| Cutoff Voltage | V _{GS(off)} | V _{DS} =10V, I _D =1mA | 0.4 | | 1.3 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} =10V, I _D =800mA | 1.3 | 2.2 | | S |
| Static Drain-to-Source On-State Resistance | R _{DS(on)1} | I _D =800mA, V _{GS} =4V | | 165 | 215 | mΩ |
| | R _{DS(on)2} | I _D =400mA, V _{GS} =2.5V | | 210 | 295 | mΩ |

Marking : ZU

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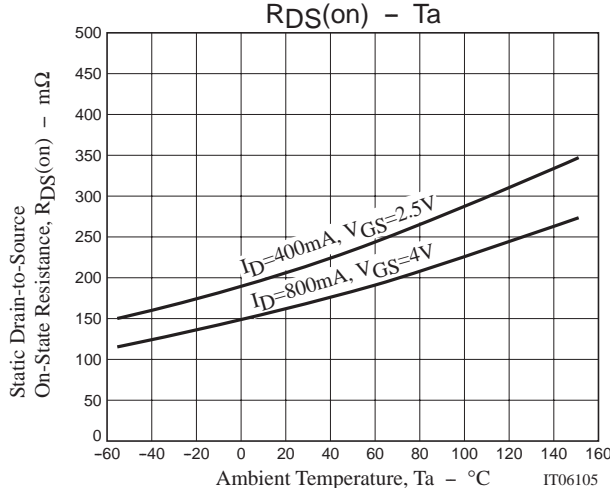
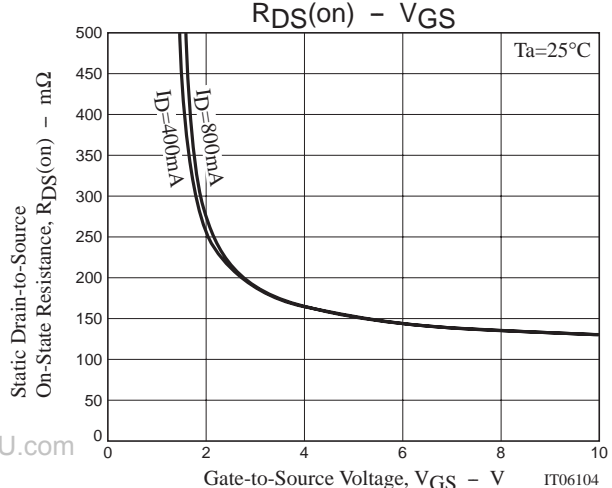
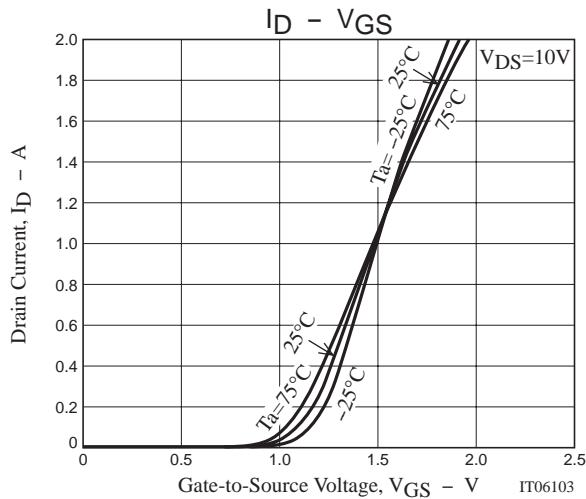
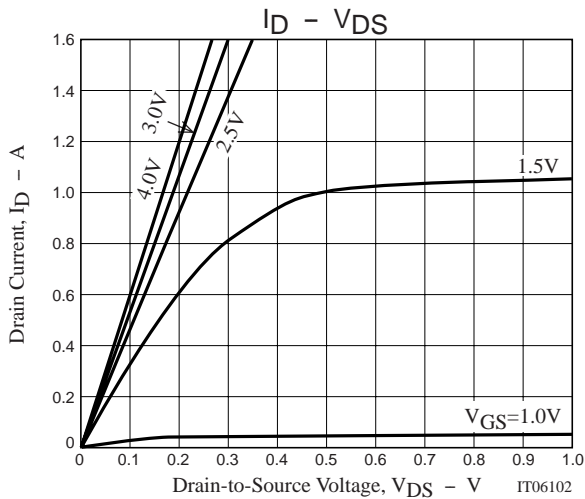
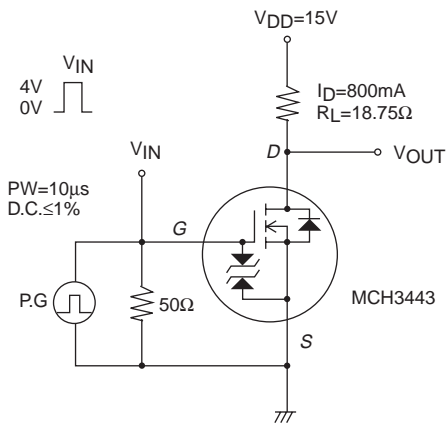
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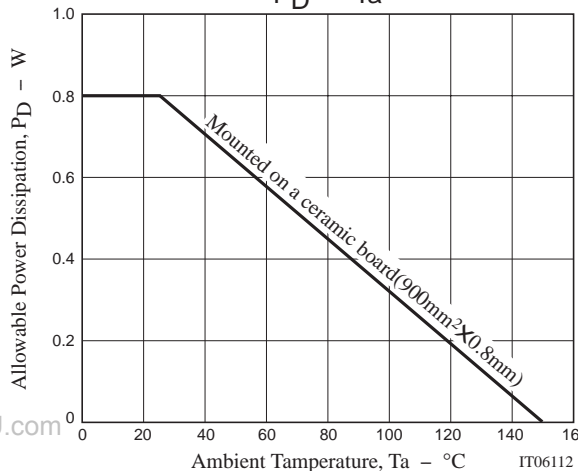
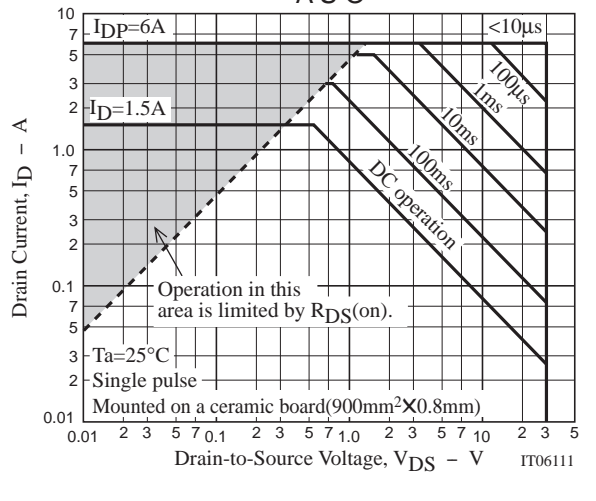
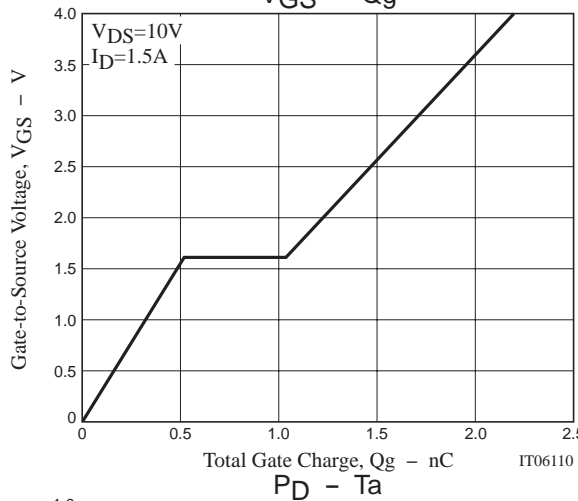
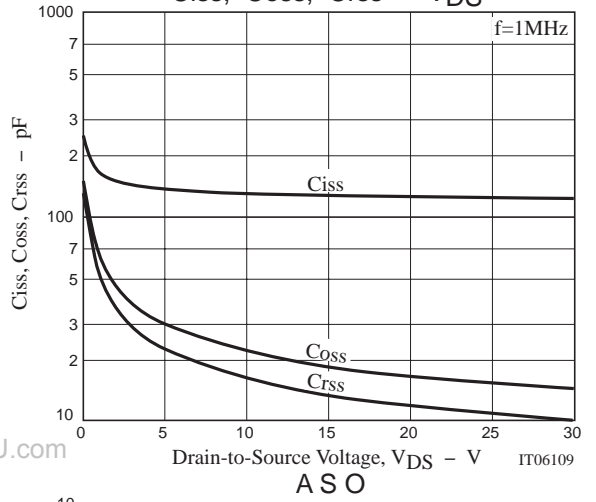
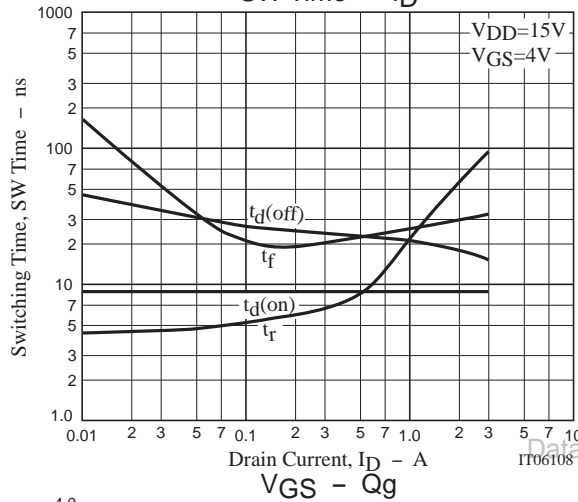
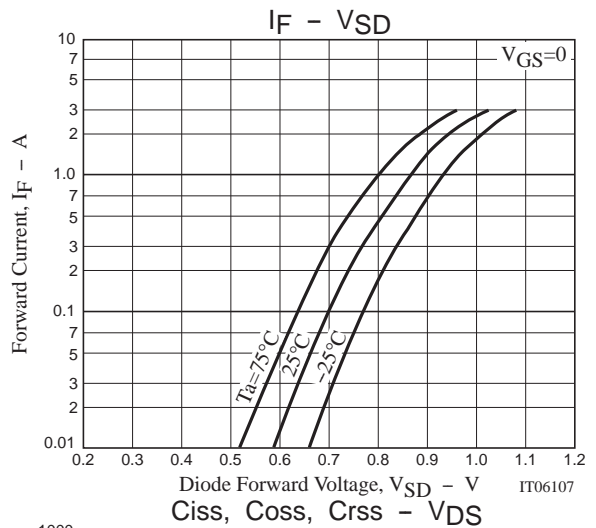
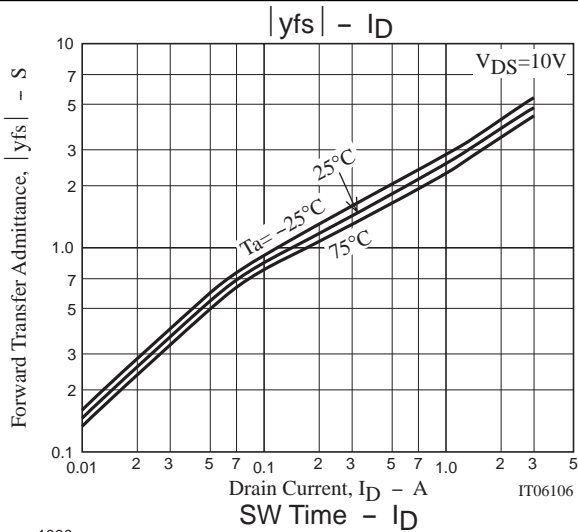
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| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-------------------------------|---------------------|---|---------|------|-----|------|
| | | | min | typ | max | |
| Input Capacitance | Ciss | V _{DS} =10V, f=1MHz | | 130 | | pF |
| Output Capacitance | Coss | V _{DS} =10V, f=1MHz | | 22 | | pF |
| Reverse Transfer Capacitance | Crss | V _{DS} =10V, f=1MHz | | 16 | | pF |
| Turn-ON Delay Time | t _{d(on)} | See specified Test Circuit | | 9 | | ns |
| Rise Time | t _r | See specified Test Circuit | | 20 | | ns |
| Turn-OFF Delay Time | t _{d(off)} | See specified Test Circuit | | 23 | | ns |
| Fall Time | t _f | See specified Test Circuit | | 29 | | ns |
| Total Gate Charge | Qg | V _{DS} =10V, V _{GS} =4V, I _D =1.5A | | 2.2 | | nC |
| Gate-to-Source Charge | Qgs | V _{DS} =10V, V _{GS} =4V, I _D =1.5A | | 0.52 | | nC |
| Gate-to-Drain "Miller" Charge | Qgd | V _{DS} =10V, V _{GS} =4V, I _D =1.5A | | 0.52 | | nC |
| Diode Forward Voltage | V _{SD} | I _S =1.5A, V _{GS} =0 | | 0.9 | 1.2 | V |

Switching Time Test Circuit



MCH3443



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